

# **Voltage Regulator**

# Adjustable Output, Low Dropout

#### 800 mA

# MC33269, NCV33269

The MC33269/NCV33269 series are low dropout, medium current, fixed and adjustable, positive voltage regulators specifically designed for use in low input voltage applications. These devices offer the circuit designer an economical solution for precision voltage regulation, while keeping power losses to a minimum.

The regulator consists of a 1.0 V dropout composite PNP–NPN pass transistor, current limiting, and thermal shutdown.

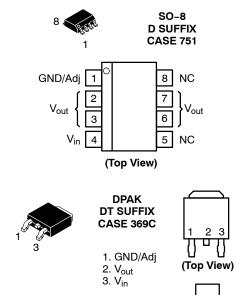
#### **Features**

- 3.3 V, 3.5 V, 5.0 V, 12 V and Adjustable Versions 2.85 V version available as MC34268
- Space Saving DPAK, SO-8 and SOT-223 Power Packages
- 1.0 V Dropout
- Output Current in Excess of 800 mA
- Thermal Protection
- Short Circuit Protection
- Output Trimmed to 1.0% Tolerance
- NCV Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q100 Qualified and PPAP Capable
- These are Pb-Free Devices

#### **DEVICE TYPE/NOMINAL OUTPUT VOLTAGE**

MC33269D	Adj	MC33269T-3.5	3.5 V
NCV33269D*	Adj	MC33269D-5.0	5.0 V
MC33269DT	Adj	MC33269DT-5.0	5.0 V
NCV33269DTRK*	Adj	NCV33269DT-5.0*	5.0 V
MC33269T	Adj	NCV33269DTRK-5.0*	5.0 V
MC33269D-3.3	3.3 V	MC33269T-5.0	5.0 V
MC33269DT-3.3	3.3 V	MC33269D-012	12 V
NCV33269DTRK-3.3*	3.3 V	MC33269DT-012	12 V
MC33269T-3.3	3.3 V	NCV33269DTRK-012*	12 V
MC33269ST-3.3	3.3 V	MC33269T-012	12 V

<sup>\*</sup>NCV Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q100 Qualified and PPAP Capable.

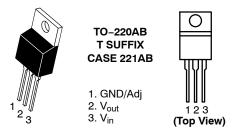


Heatsink surface (shown as terminal 4 in case outline drawing) is connected to Pin 2.

SOT-223

ST SUFFIX

CASE 318E



Heatsink surface (shown as terminal 4 in case outline drawing) is connected to Pin 2.

#### **ORDERING INFORMATION**

See detailed ordering and shipping information in the package dimensions section on page 7 of this data sheet.

#### **DEVICE MARKING INFORMATION**

See general marking information in the device marking section on page 8 of this data sheet.

#### **MAXIMUM RATINGS**

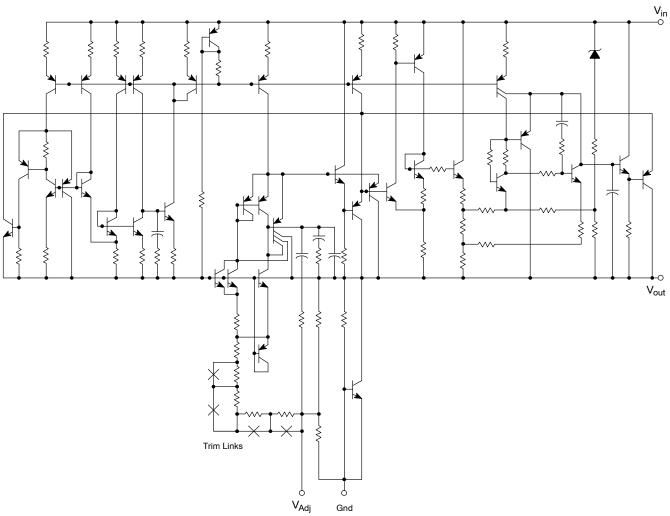
	Rating	Symbol	Value	Unit
Power Supply Input Voltage		V <sub>in</sub>	20	V
Power Dissipation				
Case 369C (DPAK)	T <sub>A</sub> = 25°C Thermal Resistance, Junction-to-Ambient Thermal Resistance, Junction-to-Case	P <sub>D</sub> θ <sub>JA</sub> θ <sub>JC</sub>	Internally Limited 92 6.0	°C/W
Case 751 (SO-8)	T <sub>A</sub> = 25°C Thermal Resistance, Junction-to-Ambient Thermal Resistance, Junction-to-Case	P <sub>D</sub> θ <sub>JA</sub> θ <sub>JC</sub>	Internally Limited 160 25	°C/W
Case 221A (TO-220)	T <sub>A</sub> = 25°C Thermal Resistance, Junction-to-Ambient Thermal Resistance, Junction-to-Case	P <sub>D</sub> θ <sub>JA</sub> θ <sub>JC</sub>	Internally Limited 65 5.0	°C/W
Case 318E (SOT-223)	T <sub>A</sub> = 25°C Thermal Resistance, Junction-to-Ambient Thermal Resistance, Junction-to-Case	P <sub>D</sub> θ <sub>JA</sub> θ <sub>JC</sub>	Internally Limited 156 15	°C/W
Operating Die Junction Tem	perature Range	TJ	-40 to +150	°C
Operating Ambient Tempera	ture Range MC33269 NCV33269	T <sub>A</sub>	-40 to +125 -40 to +125	°C
Storage Temperature		T <sub>stg</sub>	-55 to +150	°C
Electrostatic Discharge Sens	sitivity (ESD) Human Body Model (HBM) Machine Model (MM)	ESD	4000 400	V

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

## $\textbf{ELECTRICAL CHARACTERISTICS} \ (C_O = 10 \ \mu\text{F}, \ T_A = 25^{\circ}\text{C}, \ \text{for min/max values} \ T_A = -40^{\circ}\text{C to} \ +125^{\circ}\text{C}, \ \text{unless otherwise noted.})$

Characteristic	Symbol	Min	Тур	Max	Unit
Output Voltage ( $I_{out}$ = 10 mA, $T_A$ = 25°C) 3.3 Suffix ( $V_{CC}$ = 5.3 V) 3.5 Suffix ( $V_{CC}$ = 5.5 V) 5.0 Suffix ( $V_{CC}$ = 7.0 V) 12 Suffix ( $V_{CC}$ = 14 V)	V <sub>O</sub>	3.27 3.465 4.95 11.88	3.3 3.5 5.0 12	3.33 3.535 5.05 12.12	V
Output Voltage (Line, Load and Temperature) (Note 1) $ (1.25 \text{ V} \leq \text{V}_{in} - \text{V}_{out} \leq 15 \text{ V}, \text{I}_{out} = 500 \text{ mA}) \\ (1.35 \text{ V} \leq \text{V}_{in} - \text{V}_{out} \leq 10 \text{ V}, \text{I}_{out} = 800 \text{ mA}) \\ 3.3 \text{ Suffix} \\ 3.5 \text{ Suffix} \\ 5.0 \text{ Suffix} \\ 12 \text{ Suffix} $	Vo	3.23 3.43 4.90 11.76	3.3 3.5 5.0 12	3.37 3.57 5.10 12.24	V
Reference Voltage for Adjustable Voltage (I <sub>out</sub> = 10 mA, V <sub>in</sub> – V <sub>out</sub> = 2.0 V, T <sub>A</sub> = 25°C)	$V_{ref}$	1.235	1.25	1.265	V
Reference Voltage (Line, Load and Temperature) (Note 1) for Adjustable Voltage (1.25 V $\leq$ V <sub>in</sub> $-$ V <sub>out</sub> $\leq$ 15 V, I <sub>out</sub> = 500 mA) (1.35 V $\leq$ V <sub>in</sub> $-$ V <sub>out</sub> $\leq$ 10 V, I <sub>out</sub> = 800 mA)	V <sub>ref</sub>	1.225	1.25	1.275	V
Line Regulation $(I_{out} = 10 \text{ mA}, V_{in} = [V_{out} + 1.5 \text{ V}] \text{ to } V_{in} = 20 \text{ V}, T_A = 25^{\circ}\text{C})$	Reg <sub>line</sub>	-	-	0.3	%
Load Regulation $(V_{in} = V_{out} + 3.0 \text{ V}, I_{out} = 10 \text{ mA to } 800 \text{ mA}, T_A = 25^{\circ}\text{C})$	Reg <sub>load</sub>	-	-	0.5	%
Dropout Voltage	V <sub>in</sub> – V <sub>out</sub>	- -	1.0 1.1	1.25 1.35	V
Ripple Rejection (10 $V_{pp}$ , 120 Hz Sinewave; $I_{out} = 500 \text{ mA}$ )	RR	55	-	_	dB
Current Limit $(V_{in} - V_{out} = 10 \text{ V})$	I <sub>Limit</sub>	800	-	-	mA
Quiescent Current (Fixed Output) $ (1.5 \text{ V} \le \text{V}_{out} \le 3.5 \text{ V}) \\  (5 \text{ V} \le \text{V}_{out} \le 12 \text{ V}) $	IQ	_ _	5.5 -	8.0 20	mA
Minimum Required Load Current Fixed Output Voltage Adjustable Voltage	I <sub>Load</sub>	- 8.0	- -	0 -	mA
Adjustment Pin Current	I <sub>Adj</sub>	-	_	120	μΑ

<sup>1.</sup> The MC33269–12,  $V_{in}$  –  $V_{out}$  is limited to 8.0 V maximum, because of the 20 V maximum rating applied to  $V_{in}$ .



This device contains 38 active transistors.

Figure 1. Internal Schematic

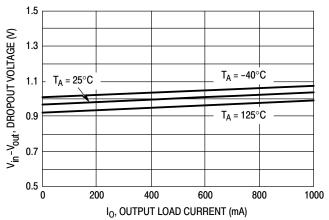


Figure 2. Dropout Voltage versus
Output Load Current

Figure 3. Transient Load Regulation

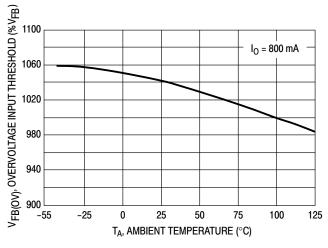


Figure 4. Dropout Voltage versus Temperature

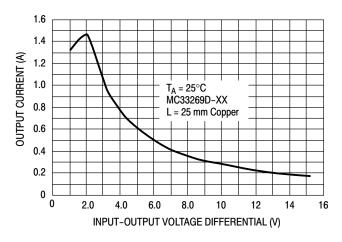


Figure 5. MC33269-XX Output DC Current versus Input-Output Differential Voltage

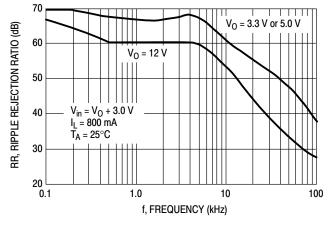


Figure 6. MC33269 Ripple Rejection versus Frequency

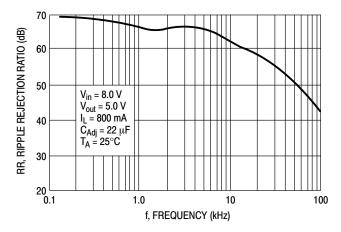


Figure 7. MC33269–ADJ Ripple Rejection versus Frequency

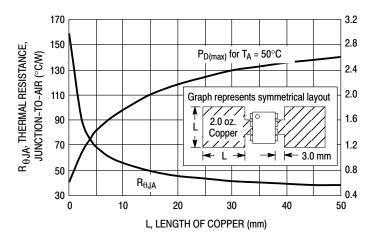


Figure 8. SOP-8 Thermal Resistance and Maximum Power Dissipation versus P.C.B. Copper Length

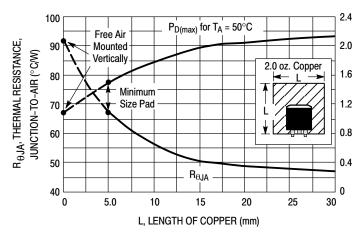


Figure 9. DPAK Thermal Resistance and Maximum Power Dissipation versus P.C.B. Copper Length

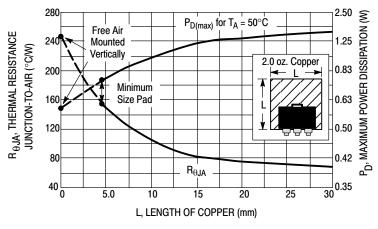


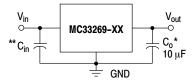
Figure 10. SOT-223 Thermal Resistance and Maximum Power Dissipation versus P.C.B. Copper Length

#### **APPLICATIONS INFORMATION**

Figures 11 through 15 are typical application circuits. The output current capability of the regulator is in excess of 800 mA, with a typical dropout voltage of less than 1.0 V. Internal protective features include current and thermal limiting.

\* The MC33269 requires an external output capacitor for stability. The capacitor should be at least 10  $\mu F$  with an equivalent series resistance (ESR) of less than 10  $\Omega$  but greater than 0.2  $\Omega$  over the anticipated operating temperature range. With economical electrolytic capacitors, cold temperature operation can pose a problem. As temperature decreases, the capacitance also decreases and the ESR increases, which could cause the circuit to oscillate. Also capacitance and ESR of a solid tantalum capacitor is more stable over temperature. The use of a low ESR ceramic capacitor placed within close proximity to the output of the device could cause instability.

\*\* An input bypass capacitor is recommended to improve transient response or if the regulator is connected to the



An input capacitor is not necessary for stability, however it will improve the overall performance.

Figure 11. Typical Fixed Output Application

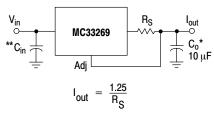
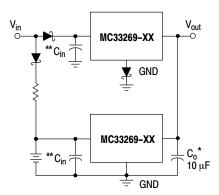


Figure 13. Current Regulator

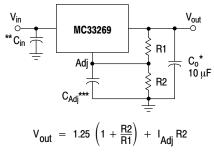


The Schottky diode in series with the ground leg of the upper regulator shifts its output voltage higher by the forward voltage drop of the diode. This will cause the lower device to remain off until the input voltage is removed.

Figure 14. Battery Backed-Up Power Supply

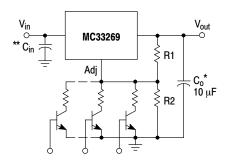
supply input filter with long wire lengths. This will reduce the circuit's sensitivity to the input line impedance at high frequencies. A  $0.33~\mu F$  or larger tantalum, mylar, ceramic, or other capacitor having low internal impedance at high frequencies should be chosen. The bypass capacitor should be mounted with shortest possible lead or track length directly across the regulator's input terminals. Applications should be tested over all operating conditions to insure stability.

Internal thermal limiting circuitry is provided to protect the integrated circuit in the event that the maximum junction temperature is exceeded. When activated, typically at 170°C, the output is disabled. There is no hysteresis built into the thermal limiting circuit. As a result, if the device is overheating, the output will appear to be oscillating. This feature is provided to prevent catastrophic failures from accidental device overheating. It is not intended to be used as a substitute for proper heat–sinking.



\*\*\*C<sub>Adj</sub> is optional, however it will improve the ripple rejection. The MC34269 develops a 1.25 V reference voltage between the output and the adjust terminal. Resistor R1, operates with constant current to flow through it and resistor R2. This current should be set such that the Adjust Pin current causes negligible drop across resistor R2. The total current with minimum load should be greater than 8.0 mA.

Figure 12. Typical Adjustable Output Application



 ${\rm R}_2$  sets the maximum output voltage. Each transistor reduces the output voltage when turned on.

Figure 15. Digitally Controlled Voltage Regulator

#### **ORDERING INFORMATION**

Device	Package	Shipping Information <sup>†</sup>
MC33269DR2G	SO-8 (Pb-Free)	2500 Units / Tape & Reel
MC33269DTRKG	DPAK (Pb-Free)	2500 Units / Tape & Reel
MC33269D-3.3G	SO-8 (Pb-Free)	98 Units / Rail
MC33269DR2-3.3G	SO-8 (Pb-Free)	2500 Units / Tape & Reel
MC33269DT-3.3G	DPAK (Pb-Free)	75 Units / Rail
MC33269DTRK-3.3G	DPAK (Pb-Free)	2500 Units / Tape & Reel
MC33269ST-3.3T3G	SOT-223 (Pb-Free)	4000 Units / Tape & Reel
MC33269T-3.3G	TO-220 (Pb-Free)	50 Units / Rail
MC33269DR2-5.0G	SO-8 (Pb-Free)	2500 Units / Tape & Reel
NCV33269DT-5.0G*	DPAK (Pb-Free)	75 Units / Rail
MC33269DTRK-5.0G	DPAK (Pb-Free)	2500 Units / Tape & Reel
NCV33269DR2G*	SO-8 (Pb-Free)	2500 Units / Tape & Reel
NCV33269DTRKG*	DPAK (Pb-Free)	2500 Units / Tape & Reel
NCV33269DTRK3.3G*	DPAK (Pb-Free)	2500 Units / Tape & Reel
NCV33269DTRK5.0G*	DPAK (Pb-Free)	2500 Units / Tape & Reel
NCV33269DTRK-12G*	DPAK (Pb-Free)	2500 Units / Tape & Reel

<sup>†</sup>For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

<sup>\*</sup>NCV Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q100 Qualified and PPAP Capable.

#### **MARKING DIAGRAMS**

SO-8 D SUFFIX CASE 751









DPAK DT SUFFIX CASE 369C

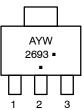






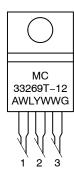


SOT-223 ST SUFFIX CASE 318E



TO-220AB T SUFFIX CASE 221A









A = Assembly Location

L, WL = Wafer Lot Y = Year

W, WW = Work Week

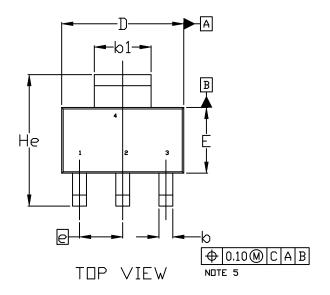
G = Pb-Free Package = Pb-Free Package

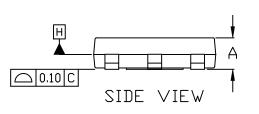
(Note: Microdot may be in either location)

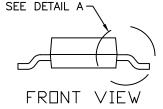


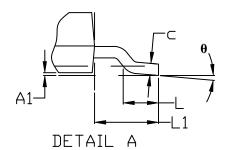
**SOT-223 (TO-261)** CASE 318E-04 ISSUE R

**DATE 02 OCT 2018** 





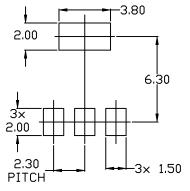




#### NOTES:

- 1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
- 2. CONTROLLING DIMENSION: MILLIMETERS
- 3. DIMENSIONS D & E DO NOT INCLUDE MOLD FLASH, PROTRUSIONS OR GATE BURRS.
  MOLD FLASH, PROTRUSIONS OR GATE BURRS SHALL NOT EXCEED 0.200MM PER SIDE.
- 4. DATUMS A AND B ARE DETERMINED AT DATUM H.
- 5. ALLIS DEFINED AS THE VERTICAL DISTANCE FROM THE SEATING PLANE TO THE LOWEST POINT OF THE PACKAGE BODY.
- 6. POSITIONAL TOLERANCE APPLIES TO DIMENSIONS 6 AND 61.

	MILLIMETERS			
DIM	MIN.	N□M.	MAX.	
Α	1.50	1.63	1.75	
A1	0.02	0.06	0.10	
b	0.60	0.75	0.89	
b1	2.90	3.06	3.20	
C	0.24	0.29	0.35	
D	6.30	6.50	6.70	
E	3.30	3.50	3.70	
е		2,30 BSC	,	
L	0.20			
L1	1.50	1.75	2.00	
He	6.70	7.00	7.30	
θ	0°		10°	



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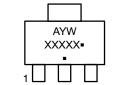
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#### SOT-223 (TO-261) CASE 318E-04 ISSUE R

**DATE 02 OCT 2018** 

STYLE 1: PIN 1. BASE 2. COLLECTOR 3. EMITTER 4. COLLECTOR	STYLE 2: PIN 1. ANODE 2. CATHODE 3. NC 4. CATHODE	STYLE 3: PIN 1. GATE 2. DRAIN 3. SOURCE 4. DRAIN	STYLE 4: PIN 1. SOURCE 2. DRAIN 3. GATE 4. DRAIN	STYLE 5: PIN 1. DRAIN 2. GATE 3. SOURCE 4. GATE
STYLE 6: PIN 1. RETURN 2. INPUT 3. OUTPUT 4. INPUT	STYLE 7: PIN 1. ANODE 1 2. CATHODE 3. ANODE 2 4. CATHODE	STYLE 8: CANCELLED	STYLE 9: PIN 1. INPUT 2. GROUND 3. LOGIC 4. GROUND	STYLE 10: PIN 1. CATHODE 2. ANODE 3. GATE 4. ANODE
STYLE 11: PIN 1. MT 1 2. MT 2 3. GATE 4. MT 2	STYLE 12: PIN 1. INPUT 2. OUTPUT 3. NC 4. OUTPUT	STYLE 13: PIN 1. GATE 2. COLLECTOR 3. EMITTER 4. COLLECTOR		

#### **GENERIC MARKING DIAGRAM\***



= Assembly Location Α

= Year

W = Work Week XXXXX = Specific Device Code

= Pb-Free Package

(Note: Microdot may be in either location) \*This information is generic. Please refer to device data sheet for actual part marking. Pb–Free indicator, "G" or microdot "•", may or may be present. Some products may

not follow the Generic Marking.

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# **MECHANICAL CASE OUTLINE**

**PACKAGE DIMENSIONS** 





#### TO-220, SINGLE GAUGE CASE 221AB-01 **ISSUE A**

**DATE 16 NOV 2010** 

- NOTES:

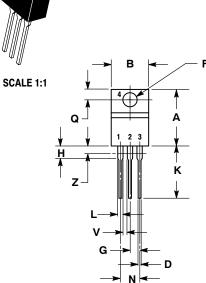
  1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.

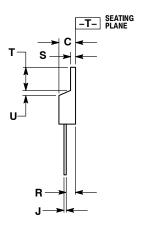
  2. CONTROLLING DIMENSION: INCHES.

  3. DIMENSION 2 DEFINES A ZONE WHERE ALL BODY AND LEAD IRREGULARTIES ARE ALLOWED.

  4. PRODUCT SHIPPED PRIOR TO 2008 HAD DIMENSIONS S = 0.045 0.055 INCHES (1.143 1.397 MM)

	INCHES MILLIMETERS			IETERS
DIM	MIN	MAX	MIN	MAX
Α	0.570	0.620	14.48	15.75
В	0.380	0.405	9.66	10.28
U	0.160	0.190	4.07	4.82
D	0.025	0.035	0.64	0.88
F	0.142	0.147	3.61	3.73
G	0.095	0.105	2.42	2.66
H	0.110	0.155	2.80	3.93
7	0.018	0.025	0.46	0.64
K	0.500	0.562	12.70	14.27
L	0.045	0.060	1.15	1.52
N	0.190	0.210	4.83	5.33
œ	0.100	0.120	2.54	3.04
R	0.080	0.110	2.04	2.79
S	0.020	0.024	0.508	0.61
T	0.235	0.255	5.97	6.47
U	0.000	0.050	0.00	1.27
٧	0.045		1.15	
Z		0.080		2.04





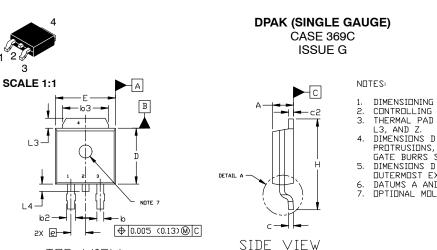
STYLE 1:		STYLE 2:		STYLE 3:	
PIN 1.	BASE	PIN 1.	BASE	PIN 1.	CATHODE
2.	COLLECTOR	2.	EMITTER	2.	ANODE
3.	EMITTER	3.	COLLECTOR	3.	GATE
4.	COLLECTOR	4.	EMITTER	4.	ANODE
STYLE 5:		STYLE 6:		STYLE 7:	
PIN 1.	GATE	PIN 1.	ANODE	PIN 1.	CATHODE
2.	DRAIN	2.	CATHODE	2.	ANODE
3.	SOURCE	3.	ANODE	3.	CATHODE
4.	DRAIN	4.	CATHODE	4.	ANODE
STYLE 9:		STYLE 10:		STYLE 11:	
PIN 1.	GATE	PIN 1.	GATE	PIN 1.	DRAIN
2.	COLLECTOR	2.	SOURCE	2.	SOURCE
3.	EMITTER	3.	DRAIN	3.	GATE
4.	COLLECTOR	4.	SOURCE	4.	SOURCE

 MAIN TERMINAL 1 MAIN TERMINAL 2 GATE MAIN TERMINAL 2
 CATHODE ANODE EXTERNAL TRIP/DELAY ANODE

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DESCRIPTION:	TO-220, SINGLE GAUGE		PAGE 1 OF 1	

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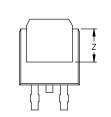
**DATE 31 MAY 2023** 

- DIMENSIONING AND TOLERANCING ASME Y14.5M, 1994. CONTROLLING DIMENSION: INCHES
- THERMAL PAD CONTOUR OPTIONAL WITHIN DIMENSIONS 63,
- L3, AND Z.

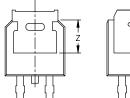
  DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH,
  PROTRUSIONS, OR BURRS. MOLD FLASH, PROTRUSIONS, OR
  GATE BURRS SHALL NOT EXCEED 0.006 INCHES PER SIDE.
  DIMENSIONS D AND E ARE DETERMINED AT THE
  OUTERMOST EXTREMES OF THE PLASTIC BODY.
  DATUMS A AND B ARE DETERMINED AT DATUM PLANE H.
  DETININAL MOLD ESCALUES.

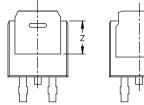
- OPTIONAL MOLD FEATURE.

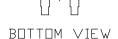
	INCHES		MILLIMETERS	
DIM	MIN.	MAX.	MIN.	MAX.
Α	0.086	0.094	2.18	2.38
A1	0.000	0.005	0.00	0.13
b	0.025	0.035	0.63	0.89
b2	0.028	0.045	0.72	1.14
b3	0.180	0.215	4.57	5.46
C	0.018	0.024	0.46	0.61
c2	0.018	0.024	0.46	0.61
D	0.235	0.245	5.97	6.22
E	0.250	0.265	6.35	6.73
e	0.090	BSC	2.29 BSC	
Н	0.370	0.410	9.40	10.41
L	0.055	0.070	1.40	1.78
L1	0.114 REF		2.90	REF
L2	0.020 BSC		0.51 BSC	
Д3	0.035	0.050	0.89	1.27
L4		0.040	-	1.01
Z	0.155		3.93	



TOP VIEW

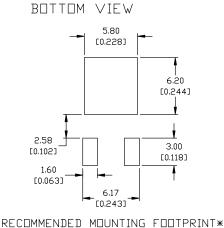




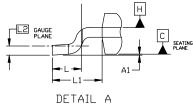


ALTERNATE

CONSTRUCTIONS

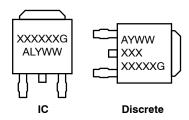


\*FOR ADDITIONAL INFORMATION ON OUR PB-FREE STRATEGY AND SOLDERING DETAILS, PLEASE DUWNLOAD THE ON SEMICONDUCTOR SOLDERING AND MOUNTING TECHNIQUES REFERENCE MANUAL, SOLDERRM/D.



CW ROTATED 90°

#### **GENERIC MARKING DIAGRAM\***



XXXXXX	= Device Code
Α	= Assembly Location
L	= Wafer Lot
Υ	= Year
WW	= Work Week
G	= Pb-Free Package

STYLE 1: PIN 1. BASE STYLE 2: PIN 1. GATE STYLE 3: PIN 1. ANODE STYLE 4: PIN 1. CATHODE STYLE 5: PIN 1. GATE 2. COLLECTOR 2. DRAIN 2. CATHODE 2. ANODE 2. ANODE 3 SOURCE 3 CATHODE 3 FMITTER 3 ANODE 3 GATE COLLECTOR 4. DRAIN CATHODE 4. ANODE ANODE

STYLE 6: STYLE 7: PIN 1. GATE 2. COLLECTOR STYLE 8: STYLE 9: STYLE 10: PIN 1. CATHODE 2. ANODE 3. CATHODE PIN 1. MT1 2. MT2 PIN 1. N/C 2. CATHODE 3. ANODE PIN 1. ANODE 2. CATHODE 3 FMITTER 3 RESISTOR ADJUST 3 GATE 4. COLLECTOR 4. CATHODE 4. ANODE CATHODE

\*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "■", may or may not be present. Some products may not follow the Generic Marking.

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DESCRIPTION:	DPAK (SINGLE GAUGE)		PAGE 1 OF 1

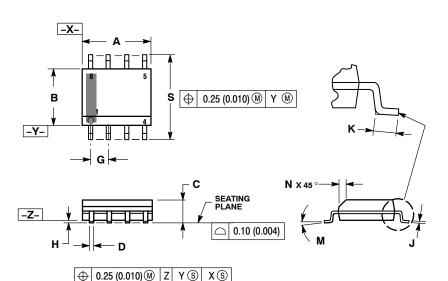
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SOIC-8 NB CASE 751-07 **ISSUE AK** 

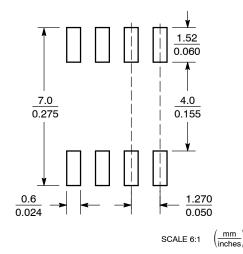
**DATE 16 FEB 2011** 



- NOTES:
  1. DIMENSIONING AND TOLERANCING PER
- ANSI Y14.5M, 1982.
  CONTROLLING DIMENSION: MILLIMETER.
- DIMENSION A AND B DO NOT INCLUDE MOLD PROTRUSION.
- MAXIMUM MOLD PROTRUSION 0.15 (0.006) PER SIDE
- DIMENSION D DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE DAMBAR PROTRUSION SHALL BE 0.127 (0.005) TOTAL IN EXCESS OF THE D DIMENSION AT MAXIMUM MATERIAL CONDITION.
- 751-01 THRU 751-06 ARE OBSOLETE. NEW STANDARD IS 751-07.

	MILLIMETERS		INCHES		
DIM	MIN	MAX	MIN	MAX	
Α	4.80	5.00	0.189	0.197	
В	3.80	4.00	0.150	0.157	
С	1.35	1.75	0.053	0.069	
D	0.33	0.51	0.013	0.020	
G	1.27 BSC		0.05	050 BSC	
Н	0.10	0.25	0.004	0.010	
J	0.19	0.25	0.007	0.010	
K	0.40	1.27	0.016	0.050	
М	0 °	8 °	0 °	8 °	
N	0.25	0.50	0.010	0.020	
S	5.80	6.20	0.228	0.244	

#### **SOLDERING FOOTPRINT\***



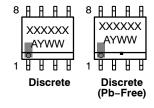
<sup>\*</sup>For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

#### **GENERIC MARKING DIAGRAM\***



XXXXX = Specific Device Code = Assembly Location = Wafer Lot = Year = Work Week

= Pb-Free Package



XXXXXX = Specific Device Code = Assembly Location Α

= Year ww = Work Week = Pb-Free Package

\*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "•", may or may not be present. Some products may not follow the Generic Marking.

#### **STYLES ON PAGE 2**

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#### SOIC-8 NB CASE 751-07 ISSUE AK

#### **DATE 16 FEB 2011**

			D, 11 2 10 1 2 D 2
STYLE 1: PIN 1. EMITTER 2. COLLECTOR 3. COLLECTOR 4. EMITTER 5. EMITTER 6. BASE 7. BASE 8. EMITTER	STYLE 2: PIN 1. COLLECTOR, DIE, #1 2. COLLECTOR, #1 3. COLLECTOR, #2 4. COLLECTOR, #2 5. BASE, #2 6. EMITTER, #2 7. BASE, #1 8. EMITTER, #1	STYLE 3: PIN 1. DRAIN, DIE #1 2. DRAIN, #1 3. DRAIN, #2 4. DRAIN, #2 5. GATE, #2 6. SOURCE, #2 7. GATE, #1 8. SOURCE, #1	STYLE 4: PIN 1. ANODE 2. ANODE 3. ANODE 4. ANODE 5. ANODE 6. ANODE 7. ANODE 8. COMMON CATHODE
STYLE 5: PIN 1. DRAIN 2. DRAIN 3. DRAIN 4. DRAIN 5. GATE 6. GATE 7. SOURCE 8. SOURCE	STYLE 6: PIN 1. SOURCE 2. DRAIN 3. DRAIN 4. SOURCE 5. SOURCE 6. GATE 7. GATE 8. SOURCE	STYLE 7: PIN 1. INPUT 2. EXTERNAL BYPASS 3. THIRD STAGE SOURCE 4. GROUND 5. DRAIN 6. GATE 3 7. SECOND STAGE Vd 8. FIRST STAGE Vd	STYLE 8: PIN 1. COLLECTOR, DIE #1 2. BASE, #1 3. BASE, #2 4. COLLECTOR, #2 5. COLLECTOR, #2 6. EMITTER, #2 7. EMITTER, #1 8. COLLECTOR, #1
STYLE 9: PIN 1. EMITTER, COMMON 2. COLLECTOR, DIE #1 3. COLLECTOR, DIE #2 4. EMITTER, COMMON 5. EMITTER, COMMON 6. BASE, DIE #2 7. BASE, DIE #1 8. EMITTER, COMMON	STYLE 10: PIN 1. GROUND 2. BIAS 1 3. OUTPUT 4. GROUND 5. GROUND 6. BIAS 2 7. INPUT 8. GROUND	STYLE 11: PIN 1. SOURCE 1 2. GATE 1 3. SOURCE 2 4. GATE 2 5. DRAIN 2 6. DRAIN 2 7. DRAIN 1 8. DRAIN 1	STYLE 12: PIN 1. SOURCE 2. SOURCE 3. SOURCE 4. GATE 5. DRAIN 6. DRAIN 7. DRAIN 8. DRAIN
STYLE 13: PIN 1. N.C. 2. SOURCE 3. SOURCE 4. GATE 5. DRAIN 6. DRAIN 7. DRAIN 8. DRAIN	STYLE 14: PIN 1. N-SOURCE 2. N-GATE 3. P-SOURCE 4. P-GATE 5. P-DRAIN 6. P-DRAIN 7. N-DRAIN 8. N-DRAIN	8. DRAIN 1  STYLE 15: PIN 1. ANODE 1 2. ANODE 1 3. ANODE 1 4. ANODE 1 5. CATHODE, COMMON 6. CATHODE, COMMON 7. CATHODE, COMMON 8. CATHODE, COMMON	STYLE 16:  PIN 1. EMITTER, DIE #1 2. BASE, DIE #1 3. EMITTER, DIE #2 4. BASE, DIE #2 5. COLLECTOR, DIE #2 6. COLLECTOR, DIE #2 7. COLLECTOR, DIE #1 8. COLLECTOR, DIE #1
STYLE 17: PIN 1. VCC 2. V2OUT 3. V1OUT 4. TXE 5. RXE 6. VEE 7. GND 8. ACC STYLE 21: PIN 1. CATHODE 1 2. CATHODE 2 3. CATHODE 3 4. CATHODE 4 5. CATHODE 5	STYLE 18: PIN 1. ANODE 2. ANODE 3. SOURCE 4. GATE 5. DRAIN 6. DRAIN 7. CATHODE 8. CATHODE STYLE 22: PIN 1. I/O LINE 1 2. COMMON CATHODE/VCC 3. COMMON CATHODE/VCC 4. I/O LINE 3 5. COMMON ANODE/GND	STYLE 19: PIN 1. SOURCE 1 2. GATE 1 3. SOURCE 2 4. GATE 2 5. DRAIN 2 6. MIRROR 2 7. DRAIN 1 8. MIRROR 1 STYLE 23: PIN 1. LINE 1 IN 2. COMMON ANODE/GND 3. COMMON ANODE/GND 4. LINE 2 IN 5. LINE 2 OUT	STYLE 20: PIN 1. SOURCE (N) 2. GATE (N) 3. SOURCE (P) 4. GATE (P) 5. DRAIN 6. DRAIN 7. DRAIN 8. DRAIN STYLE 24: PIN 1. BASE 2. EMITTER 3. COLLECTOR/ANODE 4. COLLECTOR/ANODE 5. CATHODE
<ul><li>6. COMMON ANODE</li><li>7. COMMON ANODE</li><li>8. CATHODE 6</li></ul> STYLE 25:	6. I/O LINE 4 7. I/O LINE 5 8. COMMON ANODE/GND STYLE 26: PIN 1. GND	6. COMMON ANODE/GND 7. COMMON ANODE/GND 8. LINE 1 OUT STYLE 27:	6. CATHODE 7. COLLECTOR/ANODE 8. COLLECTOR/ANODE STYLE 28:
PIN 1. VIN 2. N/C 3. REXT 4. GND 5. IOUT 6. IOUT 7. IOUT 8. IOUT STYLE 29:	2. dv/dt 2. dv/dt 3. ENABLE 4. ILIMIT 5. SOURCE 6. SOURCE 7. SOURCE 8. VCC STYLE 30:	PIN 1. ILIMIT 2. OVLO 3. UVLO 4. INPUT+ 5. SOURCE 6. SOURCE 7. SOURCE 8. DRAIN	PIN 1. SW_TO_GND 2. DASIC_OFF 3. DASIC_SW_DET 4. GND 5. V_MON 6. VBULK 7. VBULK 8. VIN
PIN 1. BASE, DIE #1 2. EMITTER, #1 3. BASE, #2 4. EMITTER, #2 5. COLLECTOR, #2 6. COLLECTOR, #2 7. COLLECTOR, #1 8. COLLECTOR, #1	PIN 1. DRAIN 1 2. DRAIN 1 3. GATE 2 4. SOURCE 2 5. SOURCE 1/DRAIN 2 6. SOURCE 1/DRAIN 2 7. SOURCE 1/DRAIN 2 8. GATE 1		

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